2008 — FUJIWARA Yasufumi

Scientific Papers/Commentary Articles

1. Y. Fujiwara, S. Takemoto, T. Tokuno, K. Hidaka, H. Ichida, M. Suzuki, Y. Terai, Mechanism of excitation and relaxation in Er,O-codoped GaAs for 1.5mm light-emitting devices with extremely stable wavelength, Physica Status Solidi (a), 205(1), 64-67, 2008
2. K. Shimada, Y. Terai, S. Takemoto, K. Hidaka, Y. Fujiwara, M. Suzuki and M. Tonouchi, Terahertz radiation from Er,O-codoped GaAs surface grown by organometallic vapor phase epitaxy, Applied Physics Letters, 92(11), 111115 1-3, 2008
3. Y. Terai, K. Hidaka, T. Hiramatsu and Y. Fujiwara, Organometallic vapor phase epitaxy of Er,O-codoped GaAs using trisdipivaloylmethanatoerbium, Journal of Physics: Conference Series, 106, 012007 1-4, 2008
4. K. Yamaoka, Y. Yoshizako, Y. Terai and Y. Fujiwara, Room-temperature deposition of highly-insulating SiOCH films by plasma-enhanced chemical vapor deposition using tetraethoxysilane, Thin Solid Films, 517(2), 479-482, 2008
5. K. Fujii, K. Hidaka, D. Yamamoto, Y. Terai and Y. Fujiwara, GaAs emission from GaInP/Er,O-Co doped GaAs/GaInP laser diodes grown by organometallic vapor phase epitaxy, Physica Status Solidi, 5(9), 2716-2718, 2008
6. K. Shimada, S. Takemoto, K. Hidaka, Y. Terai, M. Tonouchi and Y. Fujiwara, Ultrafast photoexcited carrier dynamics in GaAs:Er,O by pump and probe transmission spectroscopy, Physica Status Solidi, 5(9), 2861-2863, 2008
7. A. Fujita, T. Tokuno, K. Hidaka, K. Fujii, K. Tachibana, H. Ichida, Y. Terai, Y. Kanematsu and Y. Fujiwara, Nonradiative processes at low temperature in Er,O-codoped GaAs grown by organometallic vapor phase epitaxy, Physica Status Solidi, 5(9), 2864-2866, 2008
8. K. Yamaoka, Y. Terai, T. Yamaguchi and Y. Fujiwara, Growth of transition-metal-doped ZnO films by plasma-enhanced CVD combined with RF sputtering, Physica Status Solidi, 5(9), 3125-3127, 2008
9. S. Hashimoto, Y. Terai and Y. Fujiwara, Improved initial epitaxial growth of b-FeSi2 on Si(111) substrate by Al-doping, Physica Status Solidi, 5(9), 3159-3161, 2008
10. K. Ono, M. Takemi and Y. Fujiwara, MOVPE growth parameter dependence of phase separation in miscility gap of InGaAsP, Japanease Journal of Applied Physics, 47 (2), 896-898, 2008
11. Y. Terai, K. Hidaka, K. Fujii, S. Takemoto, M. Tonouchi and Y. Fujiwara, Ultrafast carrier-capturing in GaInP/Er,O-codoped GaAs/GaInP laser diodes grown by organometallic vapor phase epitaxy, Applied Physics Letters, 93(23), 231117 1-3, 2008
12. Y. Terai, T. Tokuno and Y. Fujiwara, Electroluminescence properties of GaInP/GaAs:Er,O/GaInP

double heterostructure light-emitting diodes at low temperature, Optical Materials, in press

13. Y. Terai, S. Hashimoto, K. Noda, and Y. Fujiwara, Epitaxial growth of Al-doped β-FeSi2 on Si(111) substrate by reactive deposition epitaxy, Physica Status Solidi, in press
14. K. Yamaoka, Y. Terai, T. Yamaguchi and Y. Fujiwara, Structural and luminescent properties of Er-doped ZnO films grown by metalorganic chemical vapor deposition, Vacuum Science and Technology, in press
15. Y. Fujiwara, Y. Terai and A. Nishikawa, Development of new-type 1.5 mm light-emitting devices based on Er, O-codoped GaAs, Journal of Physics: Conference Series, in press
16. Y. Terai, K. Noda, S. Hashimoto, and Y. Fujiwara, Photoreflectance study of β-FeSi2 epitaxial films grown by molecular beam epitaxy, Journal of Physics: Conference Series, in press
17. K. Yamaoka, Y. Terai, T. Yamaguchi, H. N. Ngo, T. Gregorkiewicz, and Y. Fujiwara, Metalorganic chemical vapor deposition of Er-doped ZnO thin films with 1.54 mm photoluminescence, Journal of Physics: Conference Series, in press
18. H. Kasai, A. Nishikawa, Y. Terai and Y. Fujiwara, Luminescence Properties of Eu-implanted GaN-based Semiconductors, Journal of Physics: Conference Series, in press
19. H. Sakaguchi, T. Mishima, T. Meguro, Y. Otoki and Y. Fujiwara, Low-temperature growth of GaAs with high quality by metalorganic vapor phase epitaxy, Journal of Physics: Conference Series, in press
20. Y. Fujiwara, K. Fujii, A. Fujita, Y. Ota, Y. Ito, T. Kawasaki, K. Noguchi, T. Tsuji, A. Nishikawa and Y. Terai, Luminescence properties in Er,O-codoped GaAs light-emitting devices with double excitation mechanism, Materials Research Society, in press
21. Y. Ota, K. Fujii, Y. Ito, T. Kawasaki, K. Noguchi, T. Tsuji, Y. Terai, and Y. Fujiwara, Optical properties of GaInP/GaAs:Er,O/GaInP laser diodes grown on p-type GaAs substrates by organometallic vapor phase epitaxy, IOP Conference Series: Materials Science and Engineering, 1, 012022/1-4, 2009

Awards

1. Y. Ota, K. Fujii, Y. Ito, T. Kawasaki, K. Noguchi, T. Tsuji, Y. Terai and Y. Fujiwara, IUMRS-ICA2008 and MRS-J Encouraging Prize, 2008 年 12 月 13 日